

## **ABSTRACT OF THE DISCLOSURE**

Disclosed are an electrode of a semiconductor device and a method of forming the  
5 same. A polysilicon layer is formed on a semiconductor substrate. An amorphous silicon  
capping layer is then formed on the polysilicon layer. A silicide layer is formed on the  
capping layer. The capping layer prevents chlorine ions from diffusing downward to the  
polysilicon layer. Accordingly, abnormal growth of the polysilicon layer can be  
prevented, thus improving the stability of the electrical characteristics of a semiconductor  
10 device electrode.